



芯基科技

# MPSA60M600, MPSP60M600, MPSU60M600, MP60M600, MP60M600

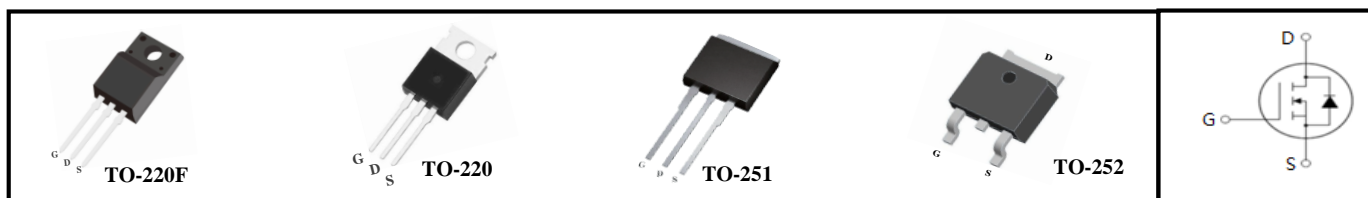


## FEATURES

- $BV_{DSS}=600V, I_D=8A$
- $R_{DS(on)}:0.6\Omega(\text{Max})@V_{GS}=10V$
- Very low FOM  $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant

## APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information		
Ordering code	Package	Marking
MPSA60M600	TO-220F	MP60M600
MPSP60M600	TO-220	MP60M600
MPSU60M600	TO-251	MP60M600
MP60M600	TO-252	MP60M600

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , unless otherwise noted				
Parameter	Symbol	Value		Unit
		TO-220F	TO-220, TO-251, TO-252	
Drain-Source Voltage ( $V_{GS} = 0V$ )	$V_{DSS}$	600		V
Continuous Drain Current	$I_D$	8		A
Pulsed Drain Current (note1)	$I_{DM}$	24		A
Gate-Source Voltage	$V_{GSS}$	$\pm 30$		V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	245		mJ
Avalanche Current (note1)	$I_{AR}$	4		A
Repetitive Avalanche Energy (note1)	$E_{AR}$	0.3		mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\dots 400V$	dv/dt	50		V/ns
Reverse diode dv/dt, $V_{DS}=0\dots 400V, I_{SD}\leq I_D$	dv/dt	50		V/ns
Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_D$	28	64	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150		$^\circ\text{C}$

Thermal Resistance				
Parameter	Symbol	Value		Unit
		TO-220F	TO-220, TO-251, TO-252	
Thermal Resistance, Junction-to-Case	$R_{thJC}$	4.5	2	K/W
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	80	62	



芯基物科技

# MPSA60M600, MPSP60M600, MPSU60M600, MPSD60M600

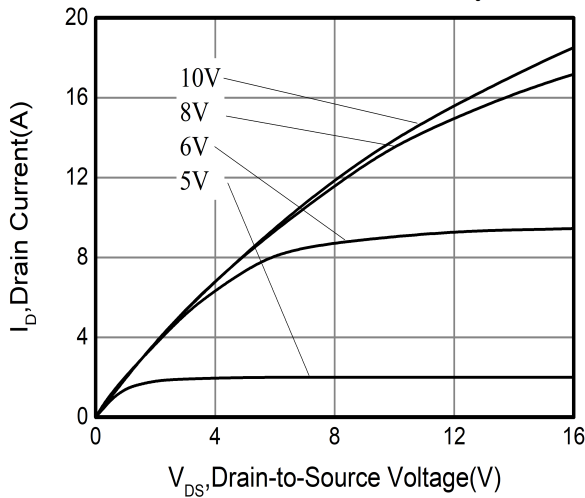
Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	600	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 600V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	$\mu A$
		$V_{DS} = 600V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	100	
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 0.25mA$	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 4A$	--	0.54	0.60	$\Omega$
Gate Resistance	$R_G$	$f = 1.0MHz, \text{open drain}$	--	14	--	$\Omega$
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 100V, f = 1.0MHz$	--	458	--	$pF$
Output Capacitance	$C_{oss}$		--	18	--	
Reverse Transfer Capacitance	$C_{rss}$		--	3	--	
Total Gate Charge	$Q_g$	$V_{DD} = 400V, I_D = 8A, V_{GS} = 10V$	--	13.4	--	nC
Gate-Source Charge	$Q_{gs}$		--	2.8	--	
Gate-Drain Charge	$Q_{gd}$		--	4	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 8A, V_{GS} = 10V, R_G = 25\Omega$	--	38	--	ns
Turn-on Rise Time	$t_r$		--	20	--	
Turn-off Delay Time	$t_{d(off)}$		--	100	--	
Turn-off Fall Time	$t_f$		--	20	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	8	A
Pulsed Diode Forward Current	$I_{SM}$		--	--	24	
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 8A, V_{GS} = 0V$	--	0.9	1.2	V
Reverse Recovery Time	$t_{rr}$	$V_R = 400V, I_F = 8A, di_F/dt = 100A/\mu s$	--	314	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	3	--	$\mu C$
Peak Reverse Recovery Current	$I_{rrm}$		--	19	--	A

## Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $I_{AS} = 4A, V_{DD} = 50V, R_G = 25\Omega, \text{Starting } T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse width  $\leq 300\mu s, \text{Duty Cycle } \leq 1\%$

Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics ( $T_J = 25^\circ\text{C}$ )



2. Transfer Characteristics

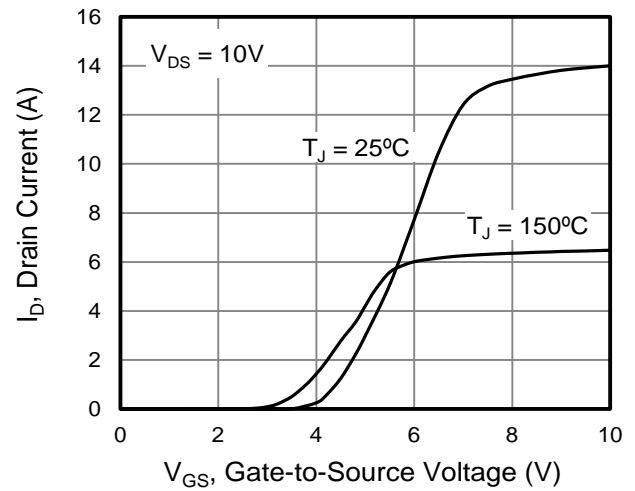


Figure 3. On-Resistance vs Drain Current

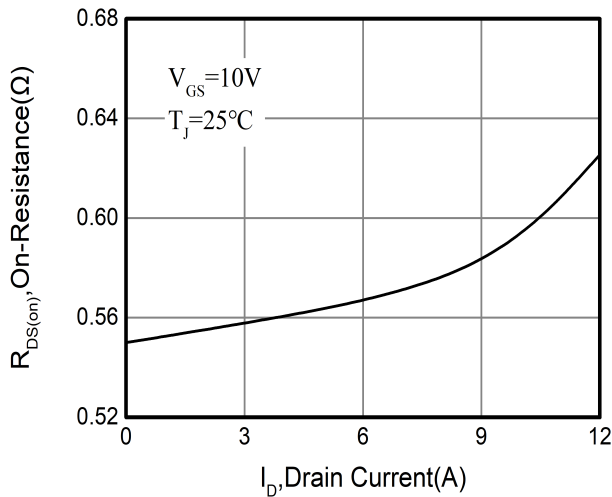


Figure 4. Capacitance

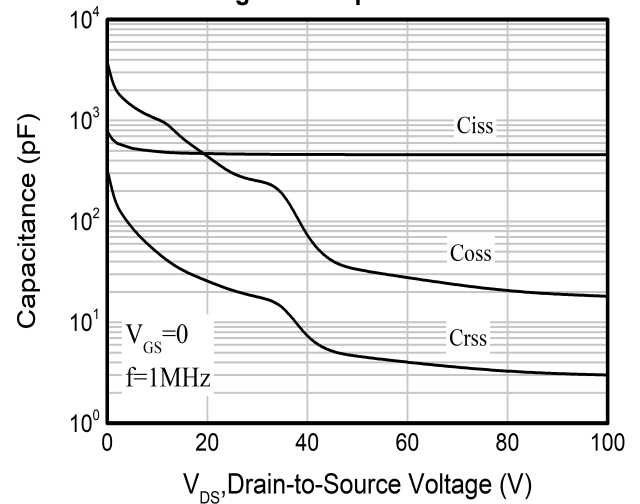


Figure 5. Gate Charge

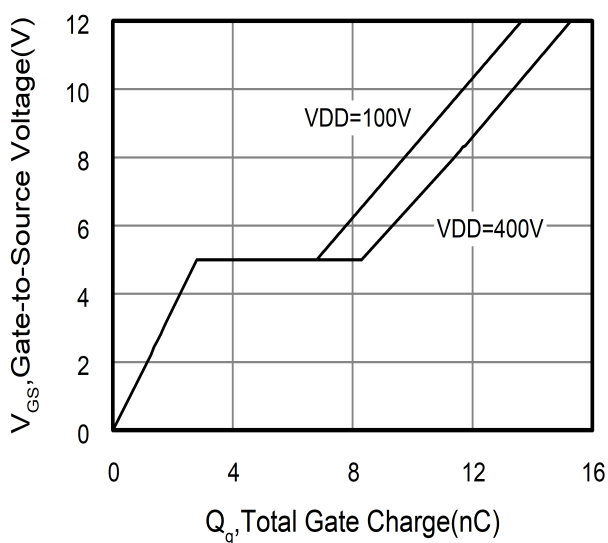
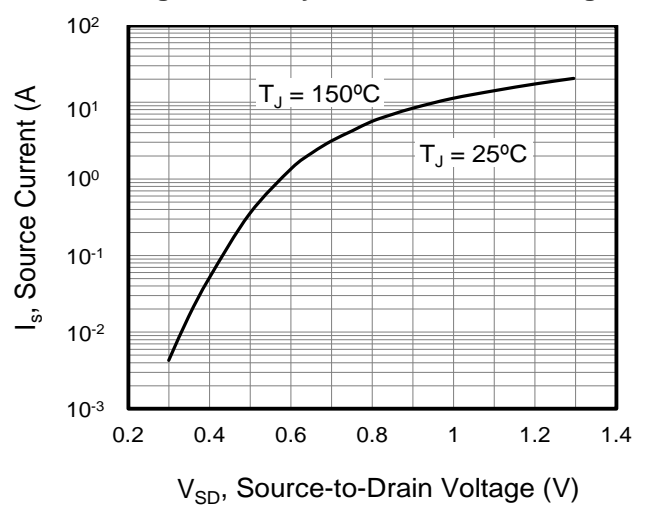


Figure 6. Body Diode Forward Voltage





芯基科技

# MPSA60M600, MPSP60M600, MPSU60M600, MPD60M600

Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

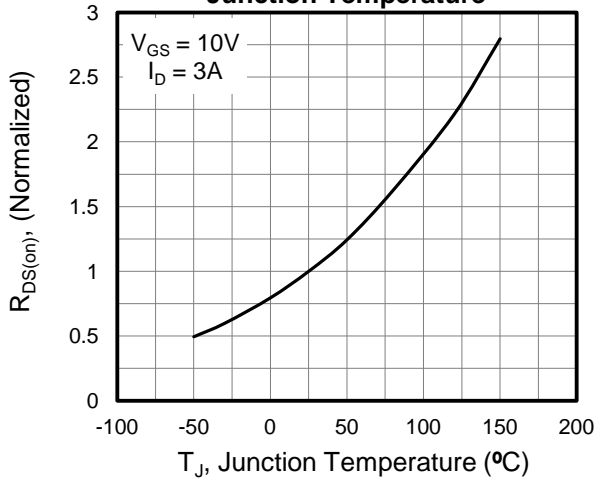


Figure 8. Threshold Voltage vs. Junction Temperature

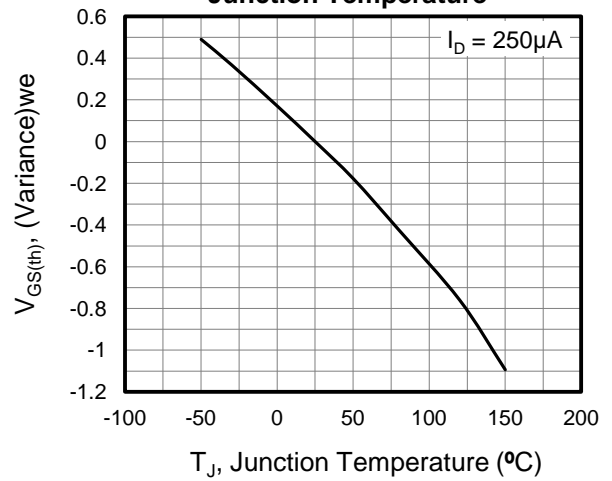


Figure 9. Transient Thermal Impedance TO-220, TO-251, TO-252

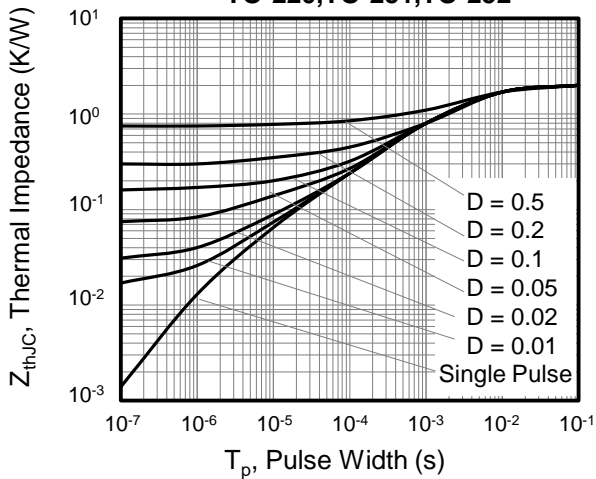


Figure 10. Transient Thermal Impedance TO-220F

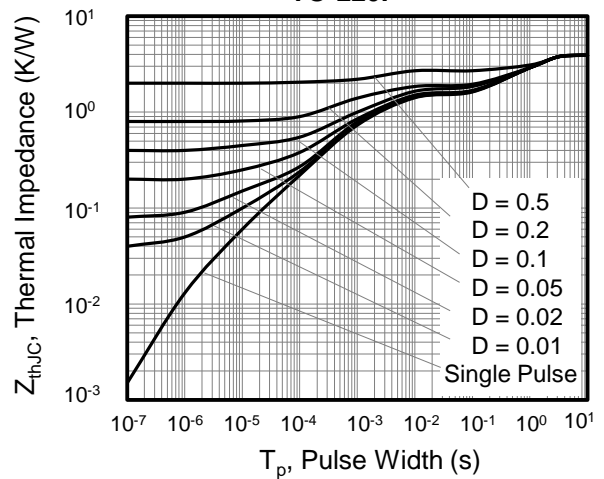


Figure A: Gate Charge Test Circuit and Waveform

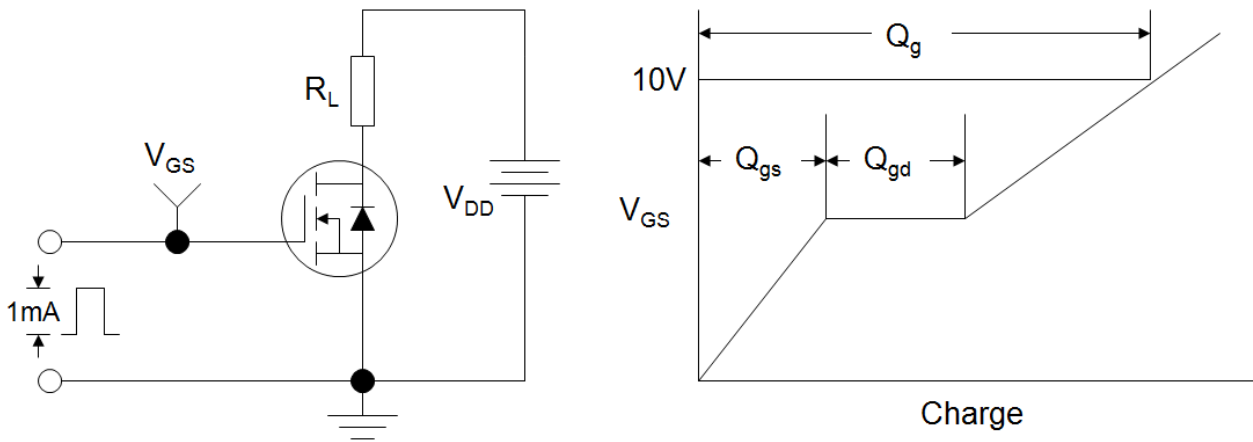


Figure B: Resistive Switching Test Circuit and Waveform

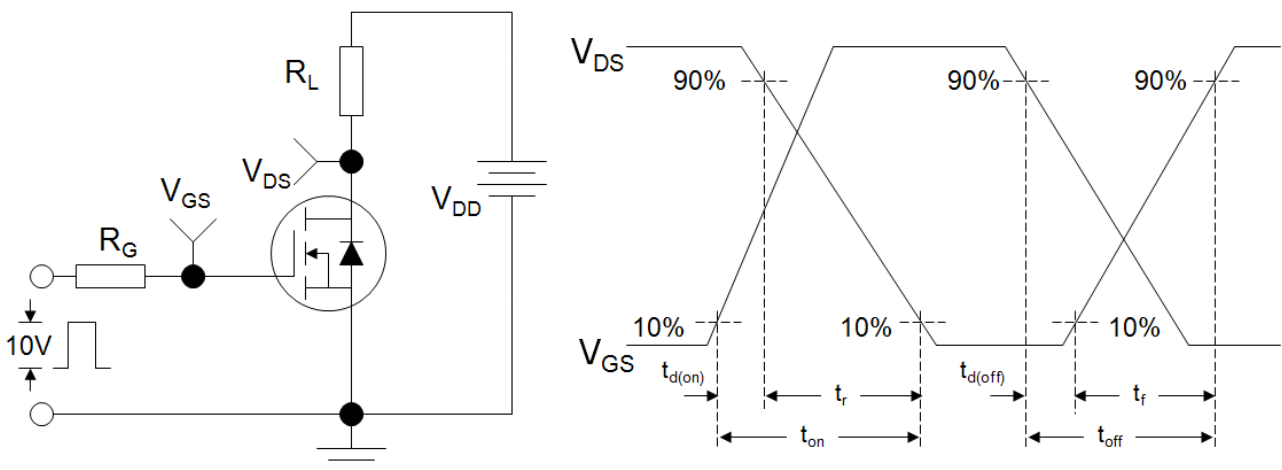
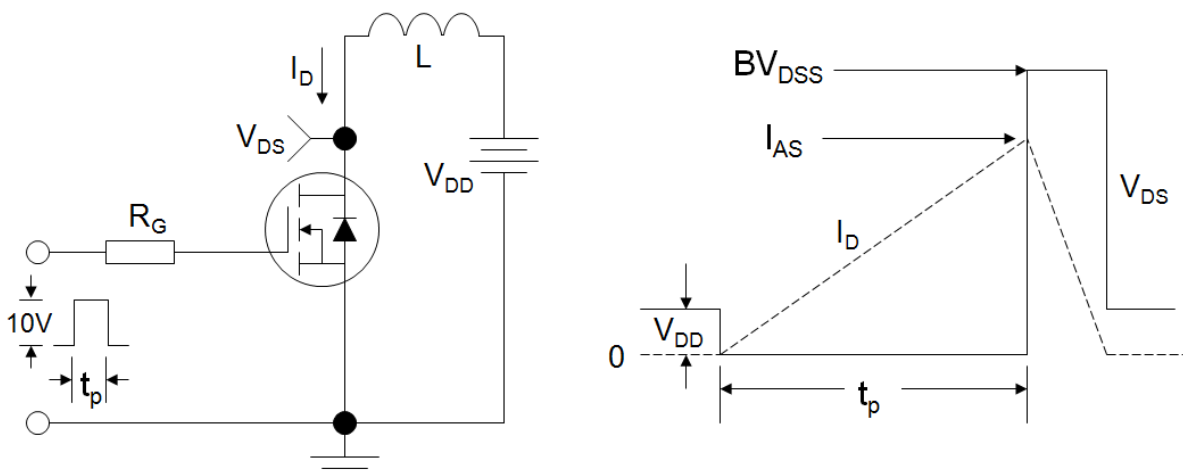
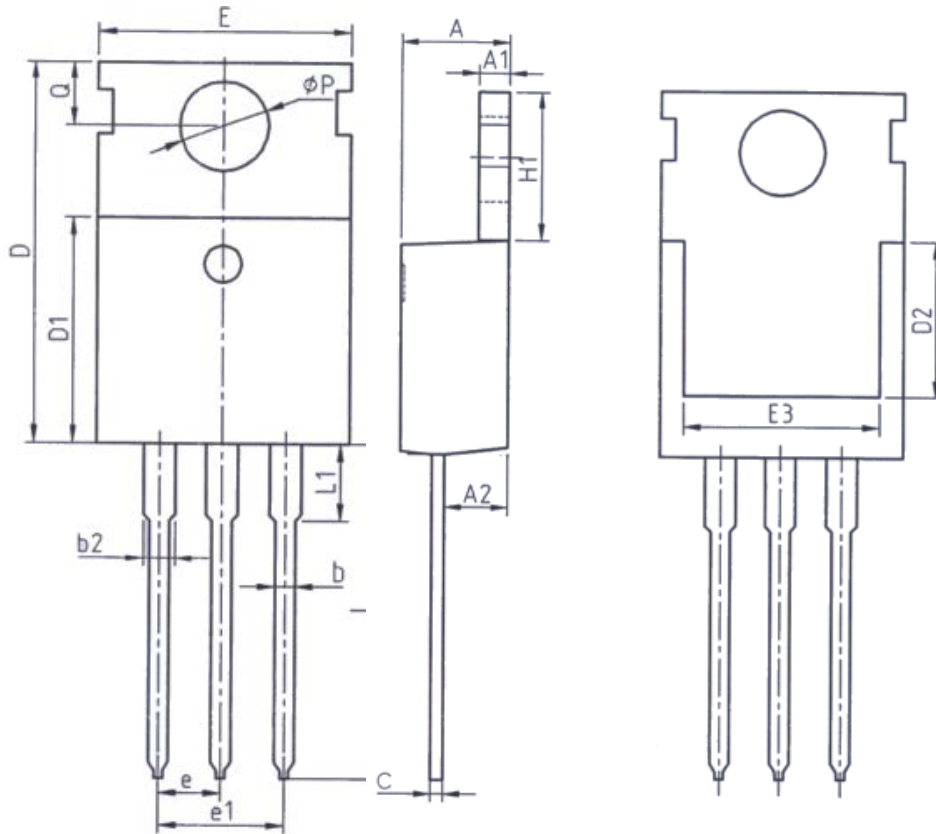


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



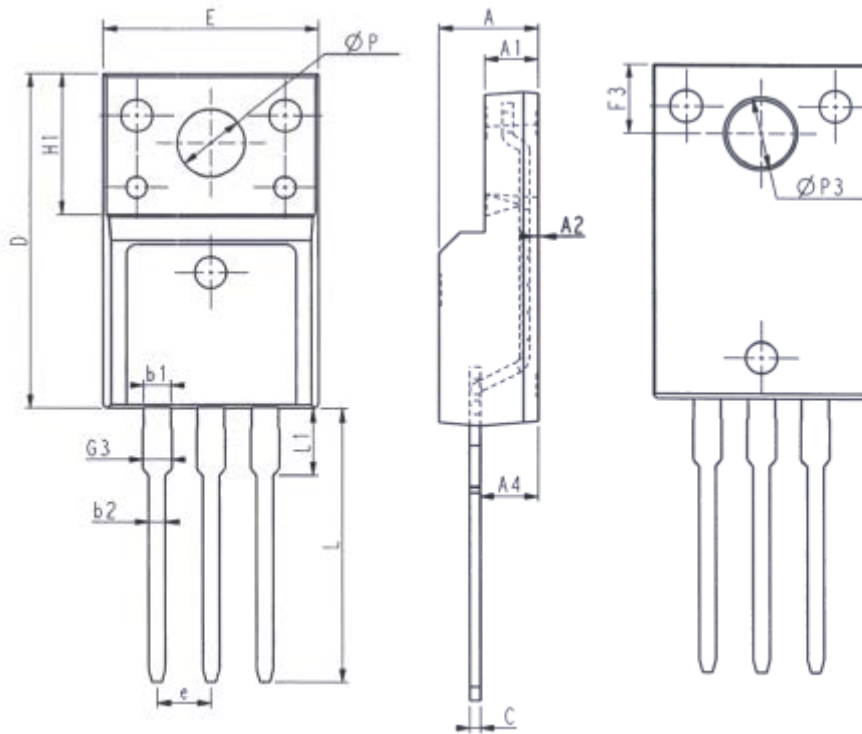
## TO-220



Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.25	1.45
A2	2.20	2.60
b	0.70	0.95
b2	1.17	1.47
c	0.40	0.65
D	15.10	16.10
D1	8.80	9.40
D2	5.50	-

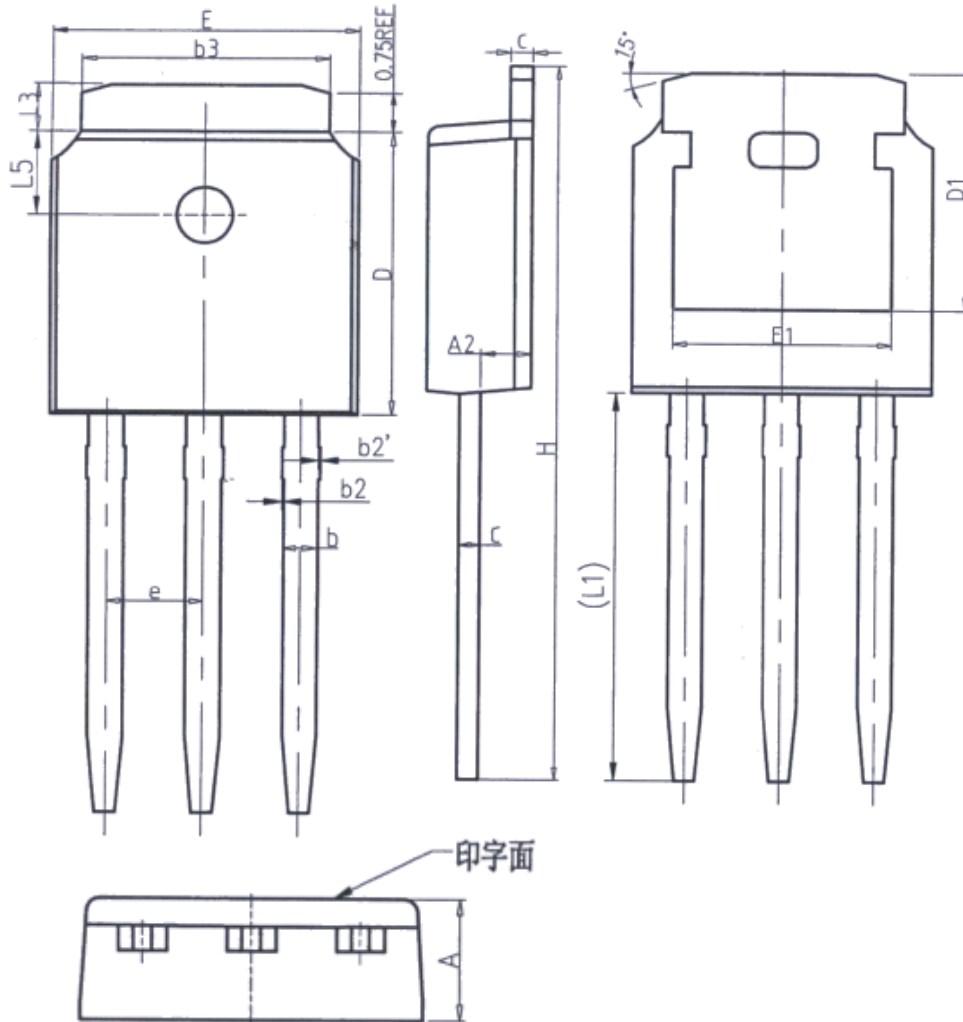
Unit: mm		
Symbol	Min.	Max.
E	9.70	10.30
E3	7.00	-
e	2.54BSC	
e1	5.08BSC	
H1	6.25	6.85
L	12.75	13.80
L1	-	3.40
P	3.40	3.80
Q	2.60	3.00

## TO-220F



Unit: mm			Unit: mm		
Symbol	Min.	Max.	Symbol	Min.	Max.
E	9.96	10.36	L	12.68	13.28
A	4.50	4.90	L1	2.93	3.13
A1	2.34	2.74	P	3.03	3.38
A2	0.30	0.60	P3	3.15	3.65
A4	2.56	2.96	F3	3.15	3.45
c	0.40	0.65	G3	1.25	1.55
D	15.57	16.17	b1	1.18	1.43
H1	6.70REF		b2	0.70	0.95
e	2.54BSC				

## TO-251

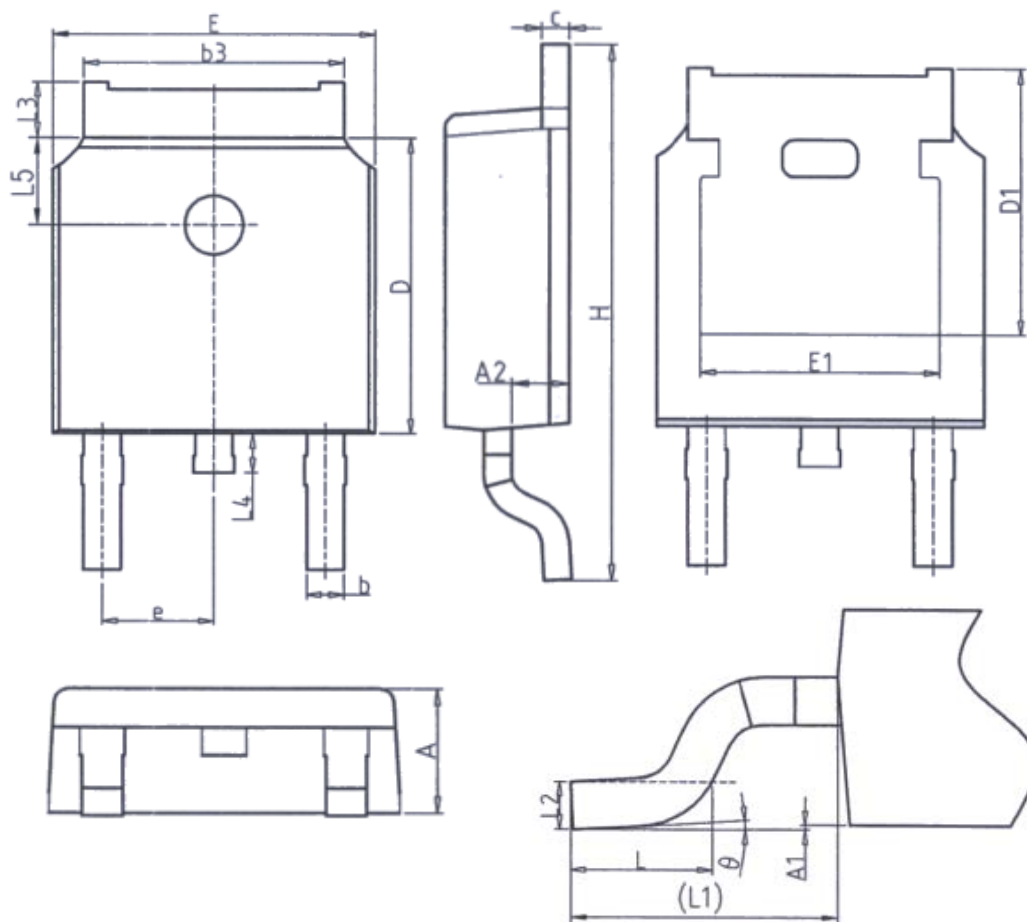


Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A2	0.97	1.17
b	0.68	0.90
b2	0.00	0.10
b2'	0.00	0.10
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22

Unit: mm		
Symbol	Min.	Max.
D1	5.30REF	
E	6.40	6.80
E1	4.63	-
e	2.286BSC	
H	16.22	16.82
L1	9.15	9.65
L3	0.88	1.28
L5	1.65	1.95



## TO-252



Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A1	0.00	0.20
A2	0.97	1.17
b	0.68	0.90
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22
D1	5.30REF	
E	6.40	6.80
E1	4.63	-

Unit: mm		
Symbol	Min.	Max.
e	2.286BSC	
H	9.40	10.50
L	1.38	1.75
L1	2.90REF	
L2	0.51BSC	
L3	0.88	1.28
L4	-	1.00
L5	1.65	1.95
θ	0°	8°